

Analog IC design (EE-320), Lecture 6

Prof. Mahsa Shoaran

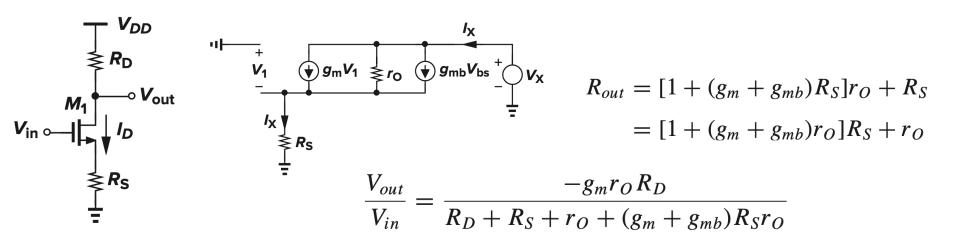
Institute of Electrical and Micro Engineering, School of Engineering, EPFL

Homework 1, TP Schedule

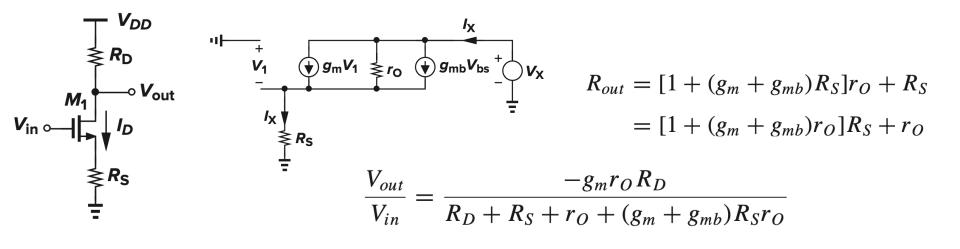
- Homework 1 assignment will be posted this week
- EDADK document to be signed and uploaded via moodle, please complete the assignment <u>by Nov 6</u>
- First TP session on Nov 11 in BC07-08 from 3:15pm to 6pm

Week	Subject by week – EE-320: Analog IC design – Fall 2024	Suggested Chapters
Week 1: 09/09 – 15/09	Introduction, organization, review of BJT and MOS transistors + Exercise1	Ch 1, Ch 2.1-2.4, Slides on Moodle
Week 2: 16/09 – 22/09	Holiday - No class	
Week 3: 23/09 – 29/09	MOS large and small-signal models, regimes of operations + Exercise2	Ch 2.1-2.4
Week 4: 30/09 – 06/10	MOS parasitic effects, layout basic, single-stage amplifiers + Exercise3	Ch 2.1-2.4, Ch 3.1
Week 5: 07/10 – 13/10	Single-stage amplifiers + Exercise4	Ch 3.1-3.7
Week 6: 14/10 – 20/10	Single-stage amplifiers + Exercise5	Ch 3.1-3.7
Week 7: 21/10 – 27/10	Holiday – No class	
Week 8: 28/10 – 03/11	Single-stage amplifiers + Cascode + Exercise6 + Homework1	Ch 4.1-4.4
Week 9: 04/11 – 10/11	Differential amplifiers + Exercise7	Ch 4.1-4.4
Week 10: 11/11 – 17/11	TP1 Practical exercise session on Cadence	Tutorial on Moodle
Week 11: 18/11 – 24/11	TP2 Practical exercise session on Cadence	Tutorial on Moodle
Week 12: 25/11 – 01/12	TP3 Practical exercise session on Cadence + Homework2	Tutorial on Moodle
Week 13: 02/12 – 08/12	TP4 Practical exercise session on Cadence	Tutorial on Moodle
Week 14: 09/12 – 15/12	Differential amplifiers, current mirrors + Exercise8	Ch 4.1-4.4, Ch 5.1-5.3
Week 15: 16/12 – 22/12	Current mirrors + Exercise9	Ch 5.1-5.3

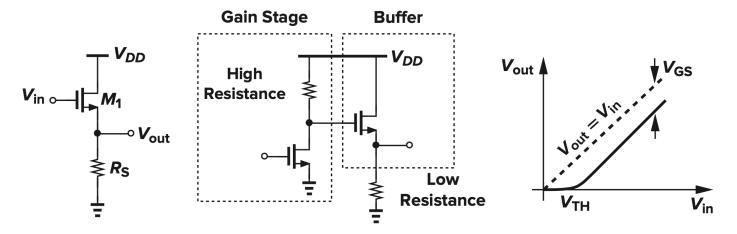
Review: Common-Source



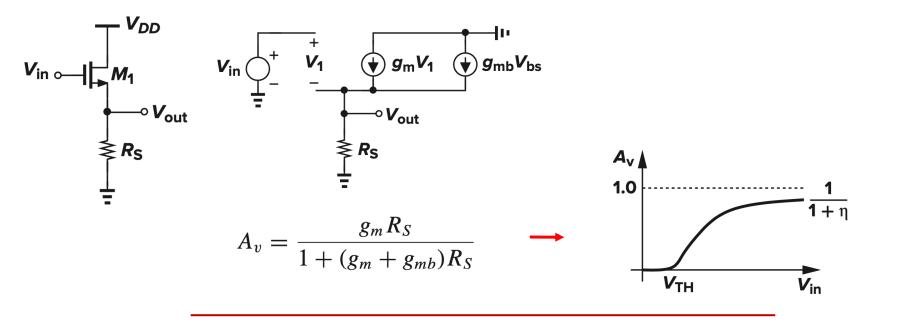
Review: Common-Source, Source-Follower

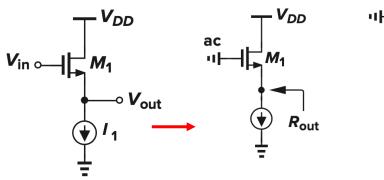


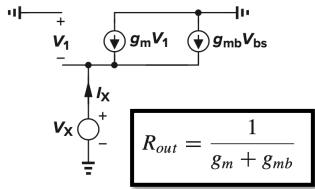
Source follower: common-drain or voltage buffer

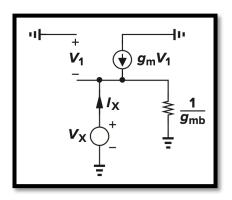


Review: Source-Follower

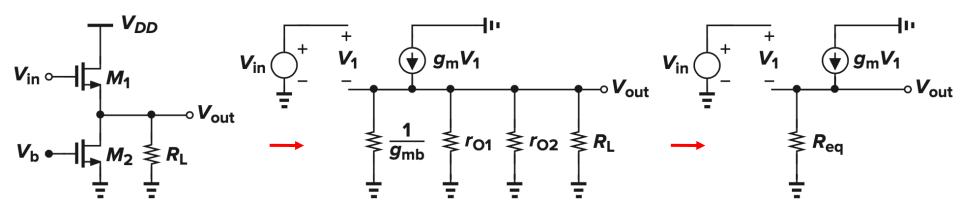








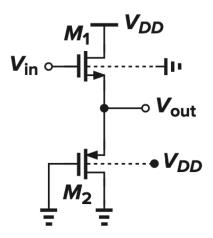
Review: Source Follower with a finite load resistance



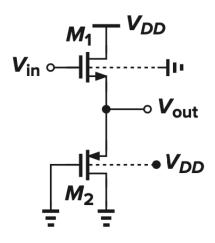
$$A_v = \frac{R_{eq}}{R_{eq} + \frac{1}{g_m}}$$
 $R_{eq} = (1/g_{mb})||r_{O1}||r_{O2}||R_L$

$$R_{eq} = (1/g_{mb})||r_{O1}||r_{O2}||R_L$$

Example: Calculate the voltage gain



Example: Calculate the voltage gain



$$A_{v} = \frac{\frac{1}{g_{m2} + g_{mb2}} ||r_{O2}||r_{O1}|| \frac{1}{g_{mb1}}}{\frac{1}{g_{mb2} + g_{mb2}} ||r_{O2}||r_{O1}|| \frac{1}{g_{mb1}} + \frac{1}{g_{m1}}}$$

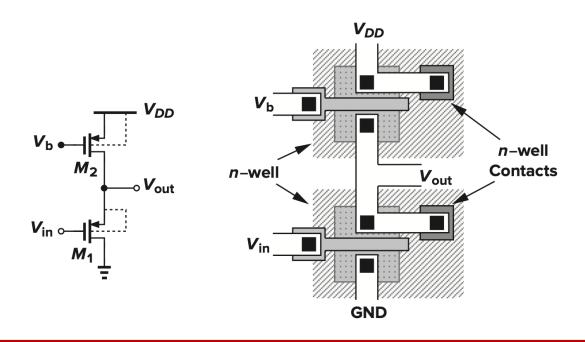
PMOS Source Follower with no body effect

- Source follower drawbacks:
 - nonlinearity
 - voltage headroom limitation
- Even if biased by an ideal current source, some nonlinearity exists due to the **nonlinear** dependence of V_{TH} upon the **source** potential

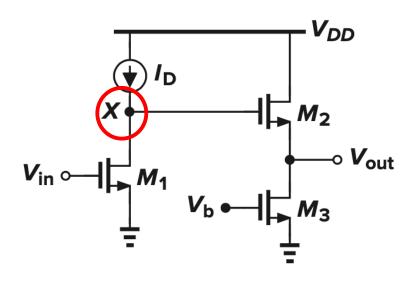
MS EE 320

PMOS Source Follower with no body effect

- Source follower drawbacks:
 - nonlinearity
 - voltage headroom limitation
- Even if biased by an ideal current source, some nonlinearity exists due to the **nonlinear** dependence of V_{TH} upon the **source** potential
- The nonlinearity due to body effect can be eliminated if the bulk is tied to source



Source Follower: a level shifter

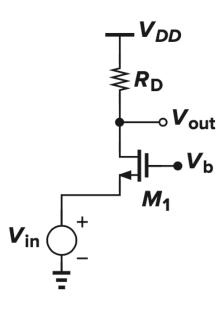


$$V_{GS1} - V_{TH1} \longrightarrow V_{GS2} + (V_{GS3} - V_{TH3})$$

- Source followers shift the dc level by V_{GS}, thereby consuming voltage headroom and limiting the swings
- One application of source followers is in performing voltage-level shift

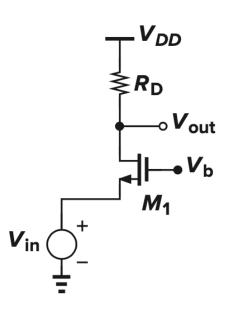
Common-Gate Stage

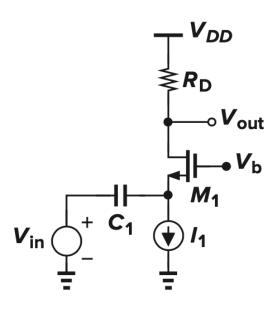
 A common-gate (CG) stage senses the input at the source and produces the output at the drain



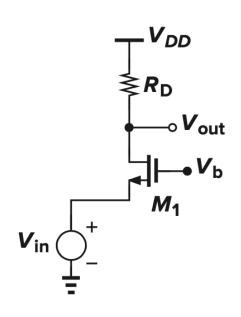
Common-Gate Stage

 A common-gate (CG) stage senses the input at the source and produces the output at the drain





Common-Gate Stage: large signal analysis



in saturation

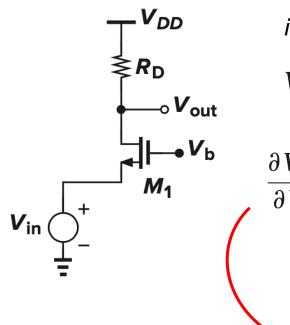
$$V_{\text{out}} \qquad I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_b - V_{in} - V_{TH})^2$$

$$V_{out} = V_{DD} - \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_b - V_{in} - V_{TH})^2 R_D$$

driving M_1 into the triode region if:

$$V_{DD} - \frac{1}{2}\mu_n C_{ox} \frac{W}{L} (V_b - V_{in} - V_{TH})^2 R_D = V_b - V_{TH}$$

Common-Gate Stage: large signal analysis



in saturation

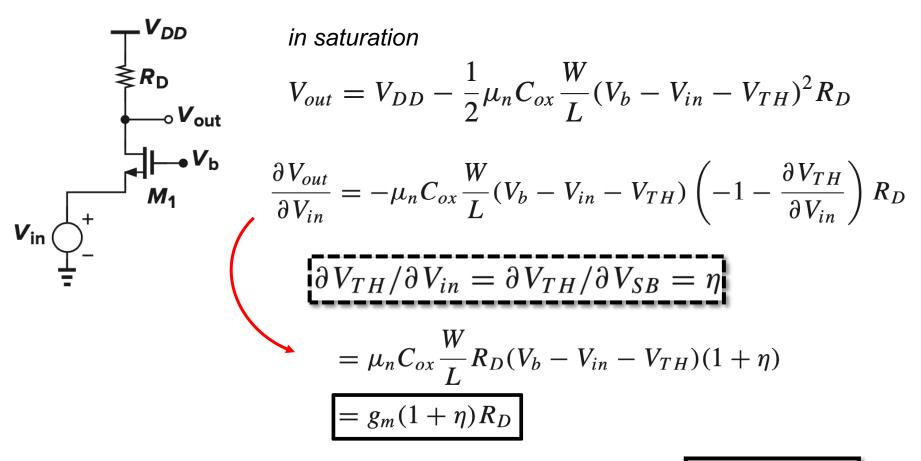
$$\frac{\partial V_{b}}{\partial I_{1}} = -\mu_{n} C_{ox} \frac{W}{L} (V_{b} - V_{in} - V_{TH}) \left(-1 - \frac{\partial V_{TH}}{\partial V_{in}}\right) R_{D}$$

$$\partial V_{TH}/\partial V_{in} = \partial V_{TH}/\partial V_{SB} = \eta$$

$$= \mu_n C_{ox} \frac{W}{L} R_D (V_b - V_{in} - V_{TH}) (1 + \eta)$$

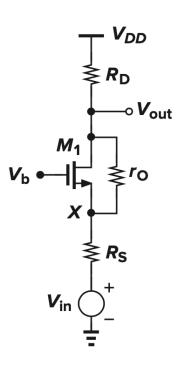
$$=g_m(1+\eta)R_D$$

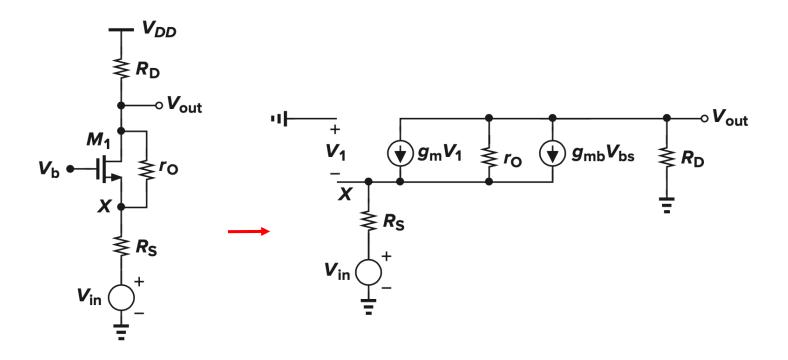
Common-Gate Stage: large signal analysis

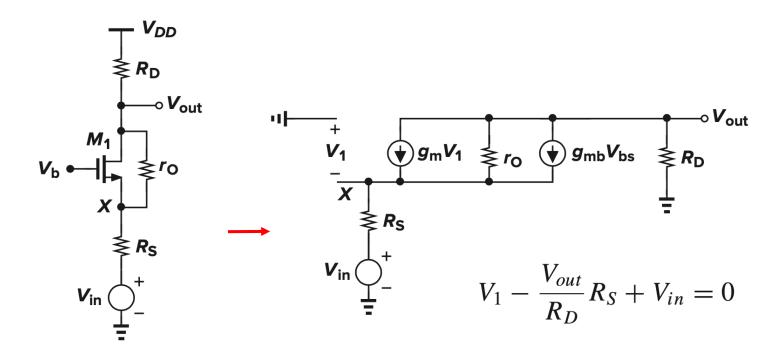


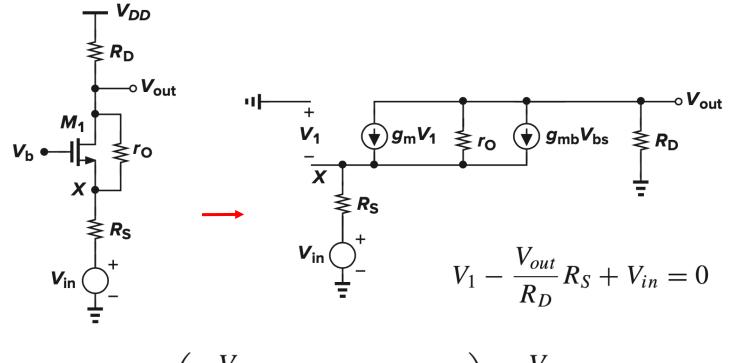
• for $\underline{\lambda = 0}$, the **input impedance** (seen at the source of M_1): $1/(g_m + g_{mb})$

 $1/[g_m(1+\eta)]$

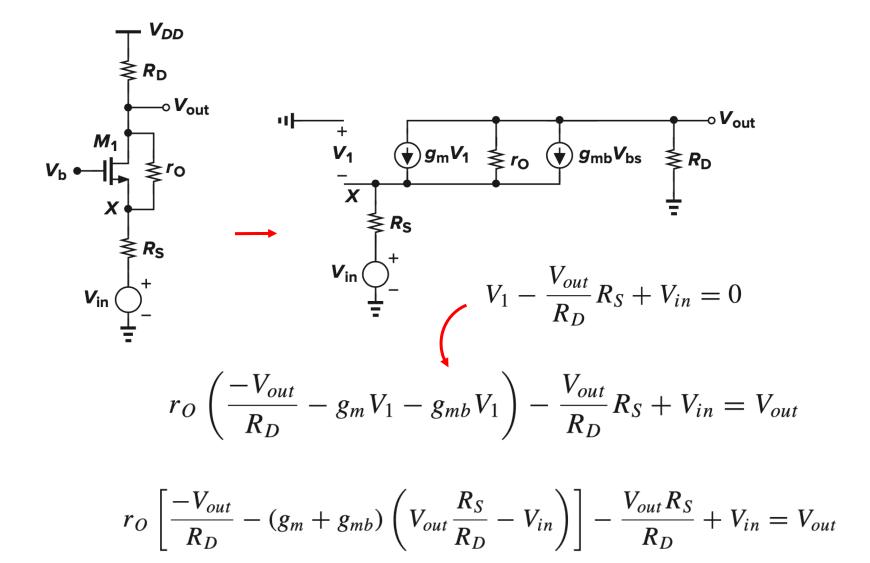


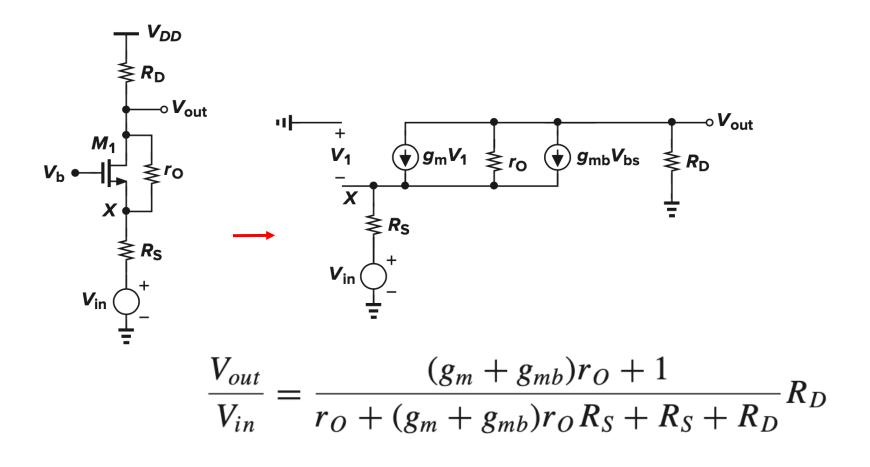


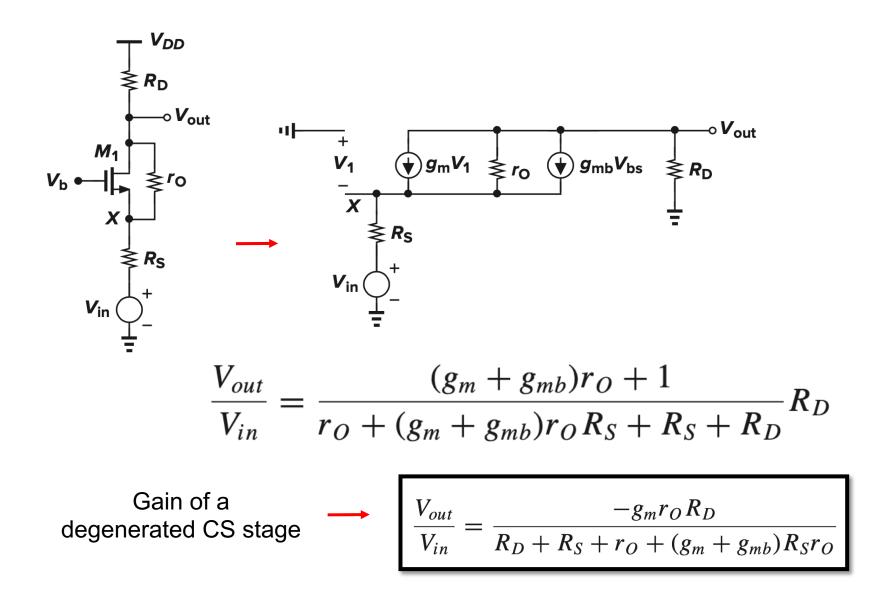


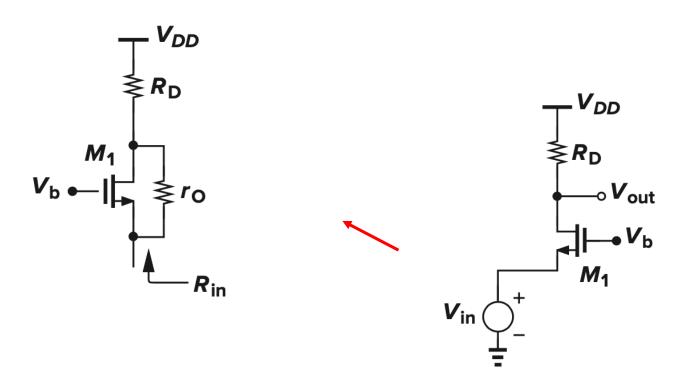


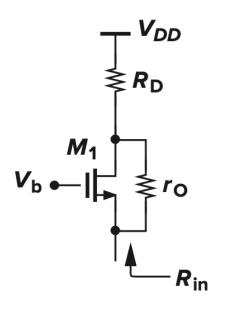
$$r_O\left(\frac{-V_{out}}{R_D} - g_m V_1 - g_{mb} V_1\right) - \frac{V_{out}}{R_D} R_S + V_{in} = V_{out}$$

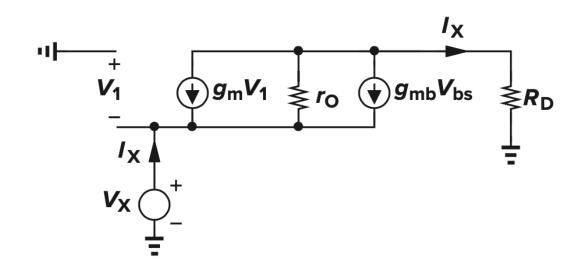










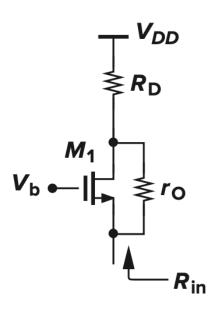


$$R_D I_X + r_O [I_X - (g_m + g_{mb})V_X] = V_X$$



$$\frac{V_X}{I_X} = \frac{R_D + r_O}{1 + (g_m + g_{mb})r_O}$$

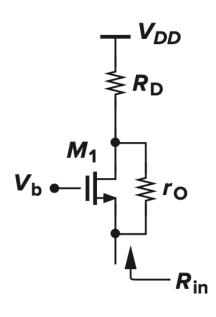
$$\approx \frac{R_D}{(g_m + g_{mb})r_O} + \frac{1}{g_m + g_{mb}}$$



$$\frac{V_X}{I_X} = \frac{R_D + r_O}{1 + (g_m + g_{mb})r_O}$$

$$\approx \frac{R_D}{(g_m + g_{mb})r_O} + \frac{1}{g_m + g_{mb}}$$

✓ the **drain impedance** is **divided** by $(g_m + g_{mb})r_O$ when seen at the **source**



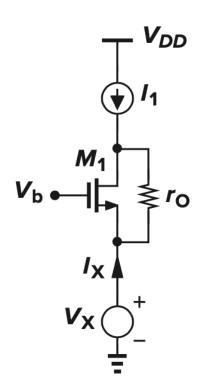
$$\frac{V_X}{I_X} = \frac{R_D + r_O}{1 + (g_m + g_{mb})r_O}$$

$$\approx \frac{R_D}{(g_m + g_{mb})r_O} + \frac{1}{g_m + g_{mb}}$$

✓ the **drain impedance** is **divided** by $(g_m + g_{mb})r_O$ when seen at the **source**

$$R_D = 0 \qquad \frac{V_X}{I_X} = \frac{r_O}{1 + (g_m + g_{mb})r_O}$$

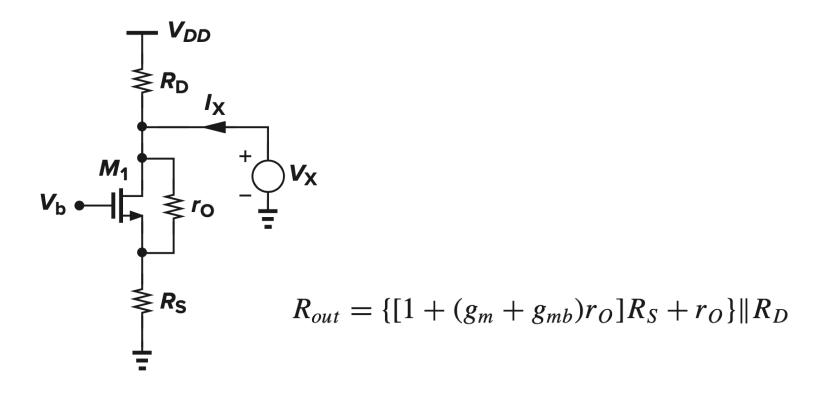
$$= \frac{1}{\frac{1}{r_O} + g_m + g_{mb}}$$



$$\frac{V_X}{I_X} = \frac{R_D + r_O}{1 + (g_m + g_{mb})r_O}$$

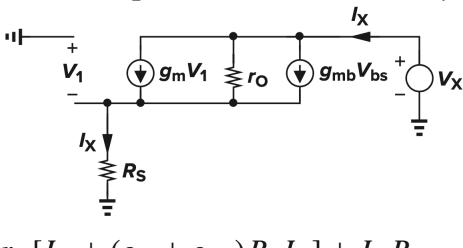
$$\approx \frac{R_D}{(g_m + g_{mb})r_O} + \frac{1}{g_m + g_{mb}}$$

the input impedance approaches infinity



Recall: Output resistance of a degenerated CS

Source degeneration increases the output resistance



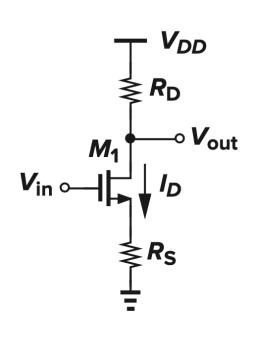
$$r_O[I_X + (g_m + g_{mb})R_SI_X] + I_XR_S = V_X$$

$$R_{out} = [1 + (g_m + g_{mb})R_S]r_O + R_S$$

$$= [1 + (g_m + g_{mb})r_O]R_S + r_O$$

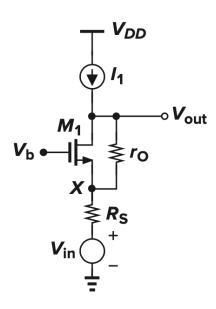
$$\approx (g_m + g_{mb})r_OR_S + r_O$$

$$= [1 + (g_m + g_{mb})R_S]r_O$$



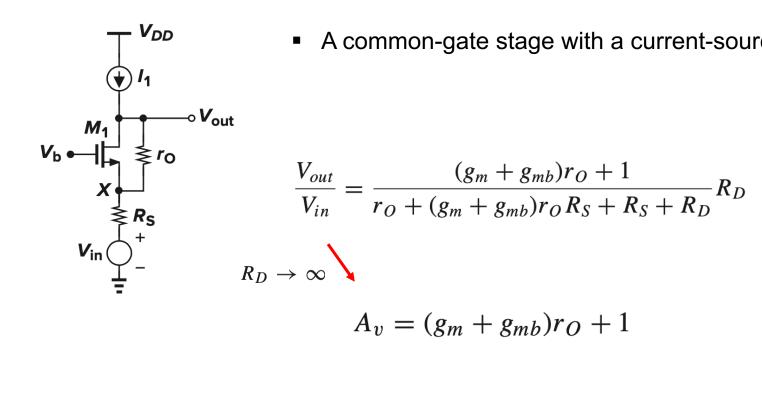
• The overall output resistance is the parallel combination of R_{out} and R_D

Example: Calculate the voltage gain



A common-gate stage with a current-source load

Example: Calculate the voltage gain



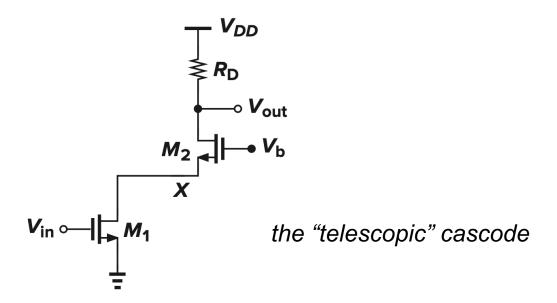
A common-gate stage with a current-source load

$$\frac{V_{out}}{V_{in}} = \frac{(g_m + g_{mb})r_O + 1}{r_O + (g_m + g_{mb})r_O R_S + R_S + R_D} R_D$$

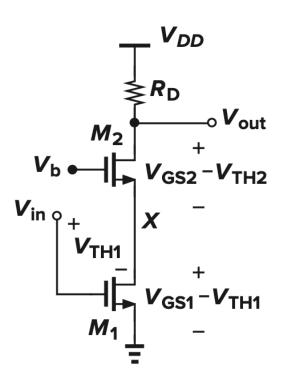
$$A_v = (g_m + g_{mb})r_O + 1$$

Cascode stage

The cascade of a CS stage and a CG stage is called a "cascode" topology, providing many useful properties.



Cascode: bias condition



$$V_{b} - V_{GS2} \ge V_{in} - V_{TH1}$$
 $V_{out} \ge V_{b} - V_{TH2}$
 \downarrow
 $V_{out} \ge V_{in} - V_{TH1} + V_{GS2} - V_{TH2}$
 $= (V_{GS1} - V_{TH1}) + (V_{GS2} - V_{TH2})$

✓ the minimum output level for both transistors to operate in saturation is
equal to the overdrive voltage of M₁ plus that of M₂

Cascode: large-signal behavior

